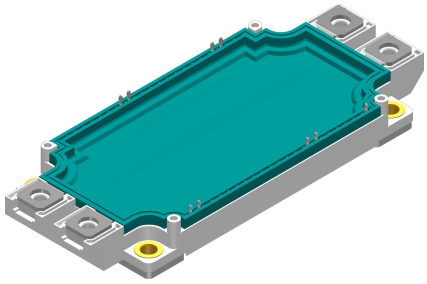
Thyristor Module

V_{RRM} = 1600 V
I_{TAV} = 150 A
V_T = 1.35 V

AC Controlling
2~ full-controlled

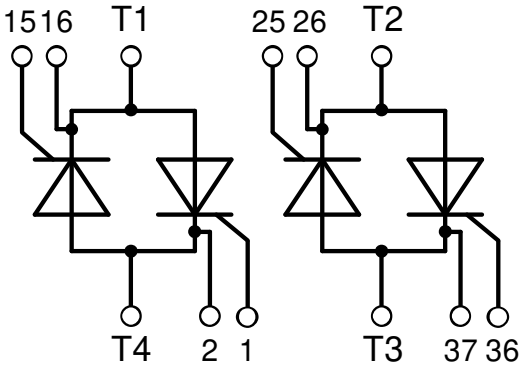
Part number

MCMA300MC1600PSF



Backside: isolated

E72873



Pin 22 = nc (not connected)

Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

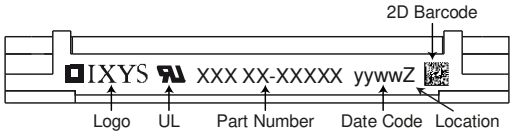
Package: SimBus F

- Isolation Voltage: 4300 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

Thyristor

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1700	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1600	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 1600 V	T_{VJ} = 25°C			300	µA
		$V_{R/D}$ = 1600 V	T_{VJ} = 150°C			20	mA
V_T	*forward voltage drop*	I_T = 150 A	T_{VJ} = 25°C			1.40	V
		I_T = 300 A				1.77	V
		I_T = 150 A	T_{VJ} = 125°C			1.35	V
		I_T = 300 A				1.79	V
I_{TAV}	*average forward current*	T_C = 100°C	T_{VJ} = 150°C			150	A
I_{RMS}	*RMS forward current per phase*	sine 180° d = 0.5				330	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.90	V
r_T	*slope resistance* }					2.92	mΩ
R_{thJC}	*thermal resistance junction to case*					0.17	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.08		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			735	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			2.40	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.59	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			2.04	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.21	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			28.8	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			27.9	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			20.8	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			20.2	kA²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		118		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 150°C; f = 50 Hz	repetitive, I_T = 450 A			150	A/µs
		t_P = 200 µs; di_G/dt = 0.45 A/µs;					
		I_G = 0.45 A; V = ⅔ V_{DRM}	non-repet., I_T = 150 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V = ⅔ V_{DRM}	T_{VJ} = 150°C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1.5	V
			T_{VJ} = -40°C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			150	mA
			T_{VJ} = -40°C			200	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150°C			0.2	V
I_{GD}	*gate non-trigger current*					10	mA
I_L	*latching current*	t_p = 30 µs	T_{VJ} = 25°C			200	mA
		I_G = 0.45 A; di_G/dt = 0.45 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			200	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0.45 A; di_G/dt = 0.45 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 150A; V = ⅔ V_{DRM}	T_{VJ} = 125 °C		350		µs
		di/dt = 10 A/µs dv/dt = 20 V/µs t_p = 200 µs					

Package SimBus F					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					300	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		125	°C
Weight						350		g
M_D	*mounting torque*				3		6	Nm
M_T	*terminal torque*				3		6	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	13.3	10.0			mm
$d_{Spb/Apb}$			*terminal to backside*	10.2	10.2			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		4300			V
		t = 1 minute			3600			V



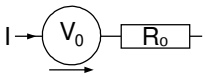
Part description

M = Module
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
300 = Current Rating [A]
MC = 2~ full-controlled
1600 = Reverse Voltage [V]
P = PressFit-Pin
SF = SimBus F

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA300MC1600PSF	MCMA300MC1600PSF	Blister	24	525675
Alternative	MCMA300MC1600PSF-PC	MCMA300MC1600PSF	Blister	24	

Equivalent Circuits for Simulation

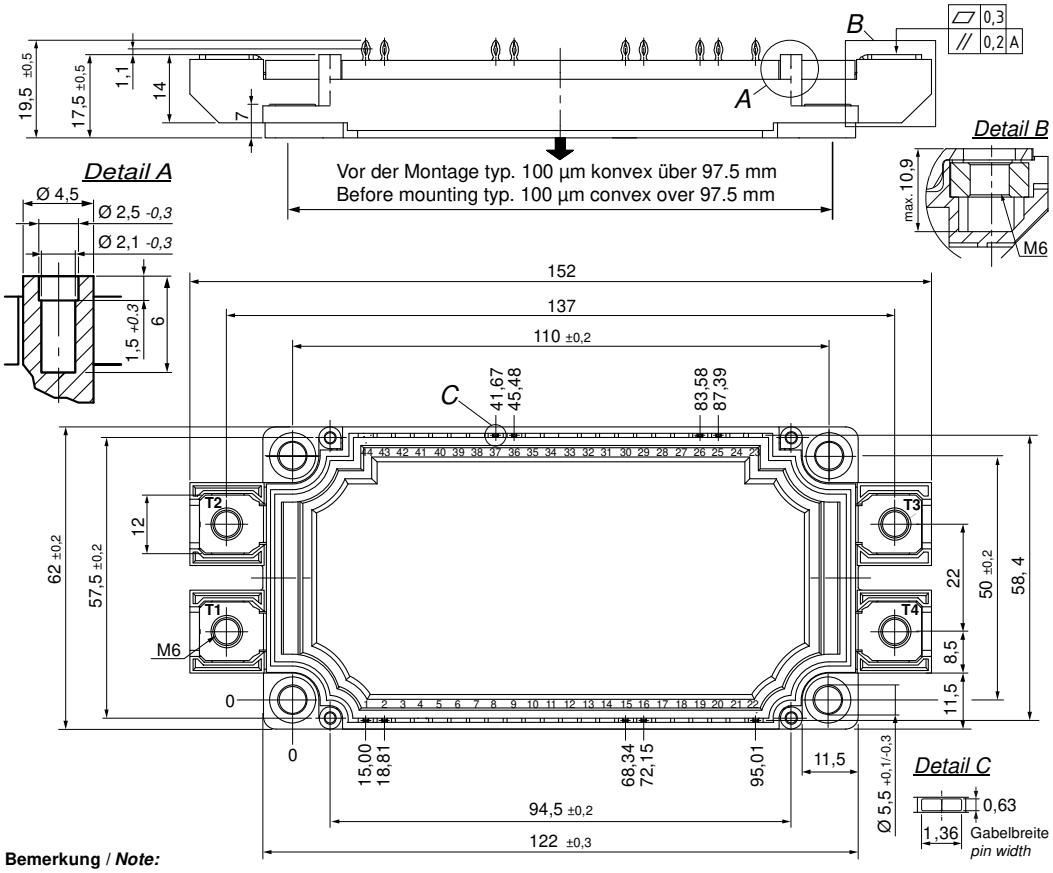
** on die level* T_{VJ} = 150°C



Thyristor

$V_{0\ max}$	*threshold voltage*	0.9	V
$R_{0\ max}$	*slope resistance **	1.48	mΩ

Outlines SimBus F

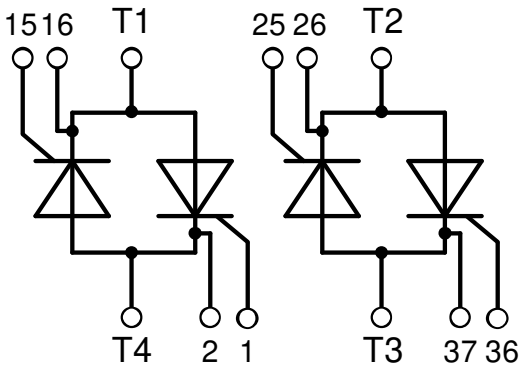


Bemerkung / ***Note:***

- Nichttolerierte Maße nach / Measure w/o tolerances acc. DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: see pin position
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern: ⌖ 0.1
- Bohrlochdurchmesser / Diameter of drill: Ø 1.16 mm
- Endlochdurchmesser / Diameter of plated holes: Ø 1.00 - 1.10 mm (Cu thickness in via typ. 50 µm)
- Beschichtung / Plating: chem. Sn max. 15 µm
- Einpresskraft / Insert Force: per terminal with a typ. insert speed of 1 mm/s: typ. 90 N
- Weitere Angaben / Further information: www.ixys.com Application note IXAN0077
- Montageanleitung / Mounting instruction: www.ixys.com Application note IXAN0024

Detail A: PCB-Montage / *Mounting on PCB*

- Empfohlene, selbstschneidende Schraube / *Recommended, self-tapping screw:* **EJOT PT®** (Größe / *size:* **K25**)
- Max. Schraubenlänge / *Max. screw length:* **PCB-Dicke** / **thickness + 6 mm** *(*max. Lochtiefe / *hole depth)*
- Empfohlenes Drehmoment / *Recommended mounting torque:* **1.5 Nm**



Pin 22 = nc (not connected)

Thyristor

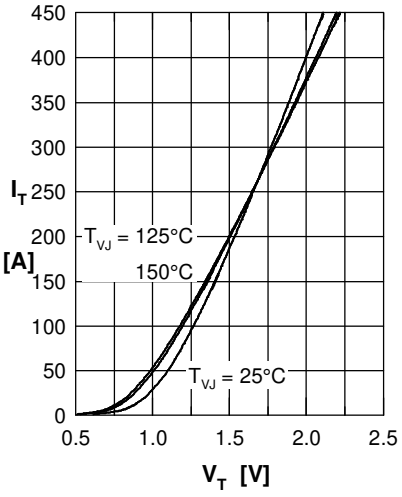


Fig. 1 Forward characteristics

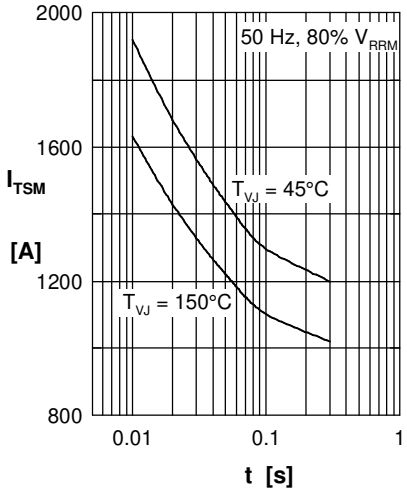


Fig. 2 Surge overload current
I_{TSM}: crest value, t: duration

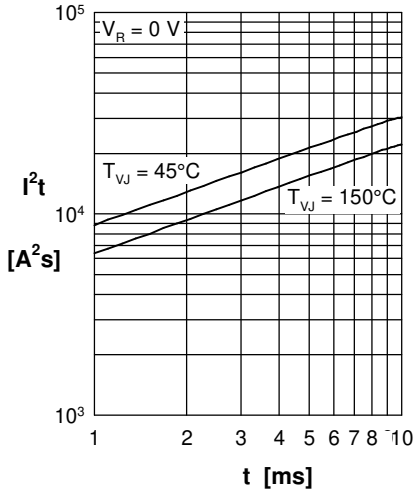


Fig. 3 I^2t versus time (1-10 s)

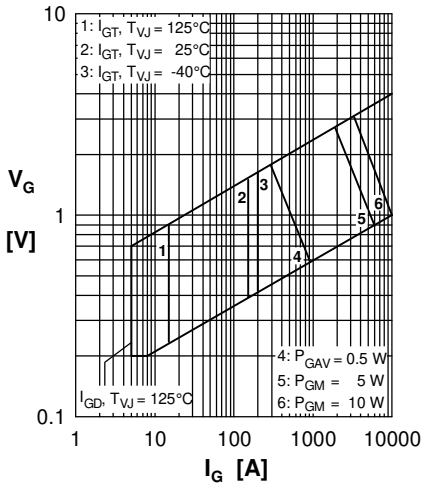


Fig. 4 Gate voltage & gate current

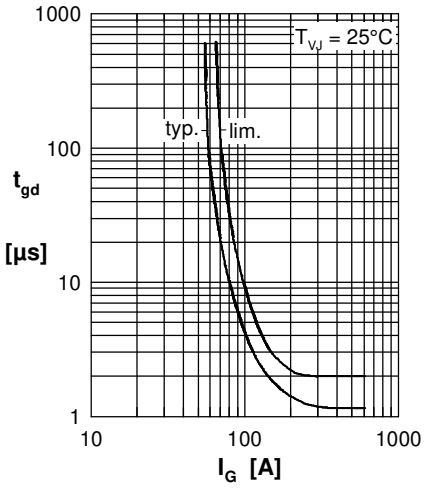


Fig. 5 Gate controlled delay time t_{gd}

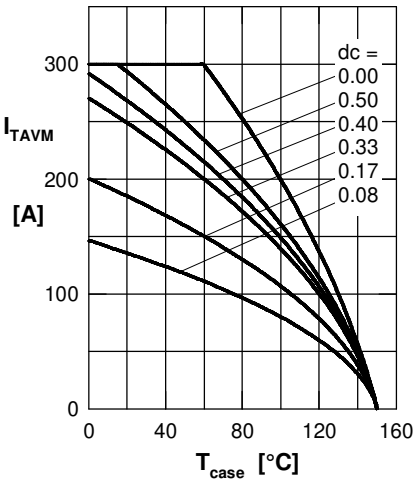


Fig. 6 Max. forward current at case temperature

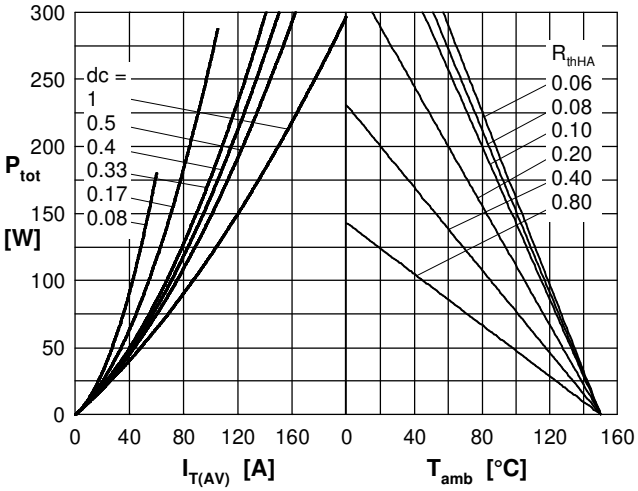
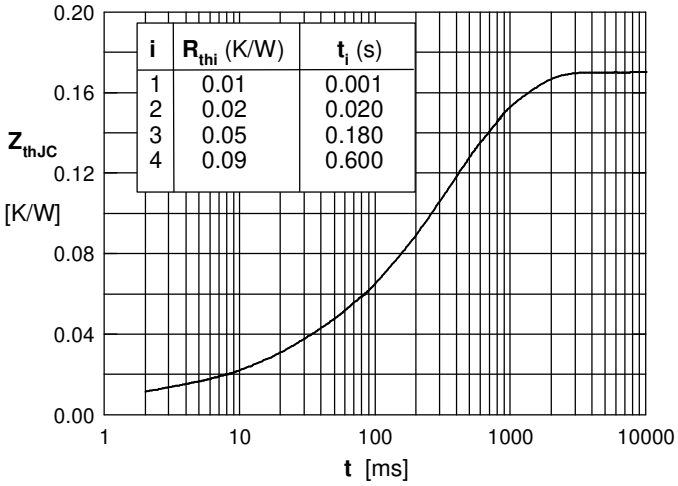


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature



i	R_{thi} (K/W)	t_i (s)
1	0.01	0.001
2	0.02	0.020
3	0.05	0.180
4	0.09	0.600

Fig. 8 Transient thermal impedance junction to case